

Abstract of the Disclosure

A method for forming word line of semiconductor device wherein a lower portion of the word line on the channel region is a I-type and a upper portion of the word line is a line-type is disclosed. The method comprises (a) forming a sacrificial insulation film on a semiconductor substrate including an active region; (b) etching the sacrificial insulation film to form an I-type sacrificial insulation film pattern whereon a channel region is to be formed; (c) forming a source/drain region; (d) forming a first interlayer insulation film; (e) planarizing the first interlayer insulation film to expose the sacrificial insulation film pattern; (f) sequentially forming a insulation film and a second interlayer insulation film; (g) etching the second interlayer insulation film and insulation film using a word line mask; (h) removing the sacrificial insulation film pattern; (i) growing a gate oxide film; (j) forming a conductive layer; and (k) planarizing the conductive layer.